

DISTRIBUTED DISC STRUCTURED MAGNETOELECTRIC COMPOSITE DEVICE IITM Technology Available for Licensing

Problem Statement

- Existing **magnetolectric devices** lack self-biased behavior and **struggle to achieve high ME coefficients efficiently**.
- There is a **need for ME devices** with enhanced **self-biased behavior and improved ME coefficients** to enable more efficient and practical applications in **micro-ME sensors and devices**.

Technology Category/ Market

Category – Magnetolectric Composite Devices

Applications – Micro Magnetolectric Sensors, Electromagnetic Signal Detection, Magnetic Field Sensing, Energy Harvesting Devices

Industry – Electronics and Semiconductor, Healthcare and Medical Devices, Automotive and Transportation, Aerospace and Defense, Energy and Renewable Energy

Market -The global magnetic sensor market was valued at USD 4.43 billion in 2021 and is expected to grow at a **CAGR of 7.5%** over the forecast period.

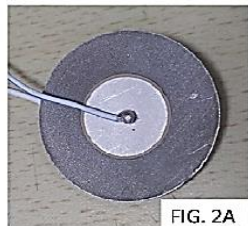


FIG. 2A



FIG. 2B



FIG. 2C



FIG. 2D

FIG. 2A illustrates a 1-disc Distributed Disc Structure (DDS) or a disc/ring configuration.

FIG. 2B illustrates a 2-discs Distributed Disc Structure (DDS) configuration.

FIG. 2C illustrates a 4-discs Distributed Disc Structure (DDS) configuration.

FIG. 2D illustrates a 6-discs Distributed Disc Structure (DDS) configuration.

Technology

Composite Material Design:

The invention employs a **unique combination of magnetostrictive and piezoelectric materials** with controlled volume fractions to create a composite material structure.

Mechanical Interference Fit:

The use of a precise mechanical interference fit, ranging from 0.3% to 1% of disc diameter, imparts prestress within the material, enabling self-biased magnetolectric behavior.

Optimized Disc Distribution:

Piezoelectric material is distributed as discs within the magnetostrictive material, enhancing the ME response.

Material Selection:

Utilizes negatively magnetostrictive materials (e.g., nickel or Samfenol-D) and specific piezoelectric materials (e.g., PZT-5A or PZT-5H) for their compatibility and properties.

Enhanced ME Coefficients:

Achieves impressive static and dynamic self-biased magnetolectric coefficients, making it suitable for various applications, including micro-ME sensors and devices

Intellectual Property

- IITM IDF Ref. 2134
- IN 387760 (PATENT GRANTED)

TRL (Technology Readiness Level)

TRL-4/5 Technology validated in lab and relevant environment

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Key Features / Value Proposition

Technical Perspective:

This invention offers enhanced ME coefficients through precise material control, enabling highly efficient ME sensors.

User Perspective:

Users benefit from improved sensitivity and reduced external requirements in ME sensors, with potential applications across industries.

Image

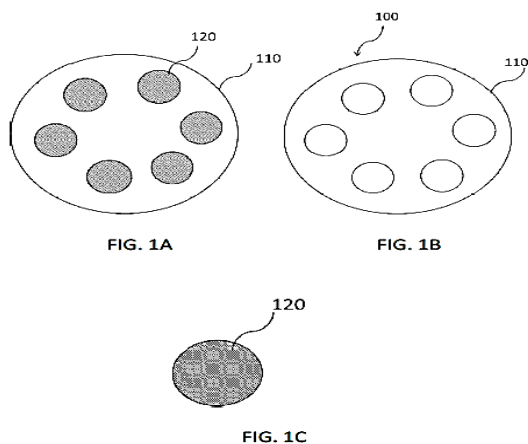


FIG. 1A illustrates the magnetoelectric composite device.

FIG. 1B illustrates the magnetostrictive material.

FIG. 1C illustrates the piezoelectric material disc.

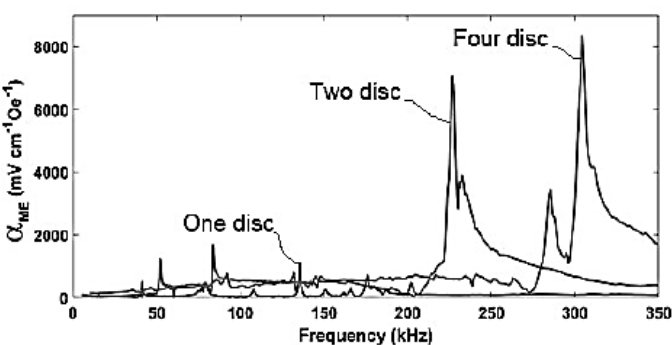


FIG. 5

FIG. 5 shows the dynamic ME coefficient of the various DDS configurations as a function of frequency.

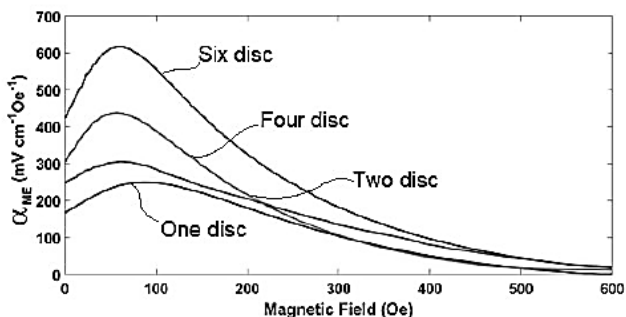


FIG. 4 illustrates the static ME experimental results obtained from the four DDS configurations.

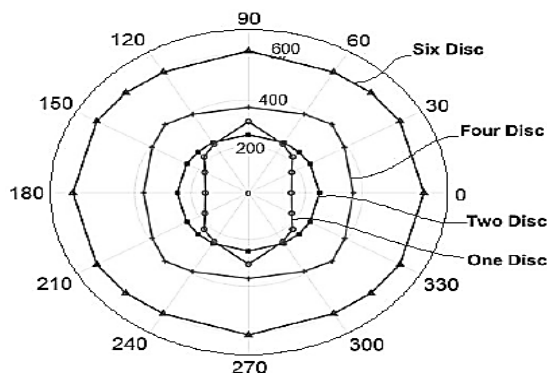


FIG. 6

FIG. 6 illustrates the polar representation of the dependence of the static ME response of various DDS configurations on their spatial placement in the magnetic field.

Research Lab

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